

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of:

Junji NOGUCHI et al.

Appln. No.:

Filed: Herewith

For: SEMICONDUCTOR DEVICE AND MANUFACTURING
METHOD THEREOF

* * *

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

Pursuant to 37 C.F.R. § 1.56, and without any
assertion as to materiality or prior art effect, the
documents listed on the attached Form PTO-1449 are hereby
cited.

Documents AQ and BJ-BK listed on the attached List are
cited in the specification, on pages 1-2, and their
relevance is indicated therein.

Documents AA-AH and BA-BB are U.S. counterparts of
Documents AI-AP and BI-BJ, respectively.

Respectfully submitted,

MWS:sjk

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March 24, 2004

By: 

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FORM PTO-1449				Atty. Docket No. XA-10063		Appln. No.	
<u>LIST OF DOCUMENTS CITED BY APPLICANT</u>				Applicant Junji NOGUCHI et al.			
				Filing Date Herewith		Group	
U.S. PATENT DOCUMENTS							
Examiner Initial		Document Number	Date	Name	Class	Sub-class	Filing Date
	AA	6,555,464	04/29/03	Fukada et al.	438	622	
	AB	2002/0127843	09/12/02	Noguchi et al.	438	622	
	AC	2001/0045651	11/29/01	Saito et al.	257	750	
	AD	2001/0030367	10/18/01	Noguchi et al.	257	758	
	AE	2002/0042193	04/11/02	Noguchi et al.	438	618	
	AF	2002/0100984	08/01/02	Oshima et al.	257	774	
	AG	2003/0030146	02/13/03	Tamaru et al.	257	762	
	AH	2003/0087513	05/08/03	Noguchi et al.	438	627	
FOREIGN PATENT DOCUMENTS							
Examiner Initial		Document Number	Date	Country	Class	Sub-class	Translation
	AI	2000-349150	12/15/00	Japan			Abstract
	AJ	2001-53076	02/23/01	Japan			Abstract
	AK	2001-319928	11/16/01	Japan			Abstract
	AL	2001-291720	10/19/01	Japan			Abstract
	AM	2002-110679	04/12/02	Japan			Abstract
	AN	2002-164428	06/07/02	Japan			Abstract
	AO	2003-60030	02/28/03	Japan			Abstract
	AP	2003-142579	05/16/03	Japan			Abstract
OTHER (including author, title, date, pertinent pages, etc.)							
	AQ	Chiang et al., "TDDB Reliability Improvement in Cu Damascene by using a Bilayer-Structured PECVC SiC Dielectric Barrier", IEEE 2002 International Interconnect Technology Conference, June 3-5, 2002, pp. 200-202.					
Examiner				Date Considered			
EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.							

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<u>LIST OF DOCUMENTS CITED BY APPLICANT</u>				Applicant Junji NOGUCHI et al.			
				Filing Date Herewith		Group	
U.S. PATENT DOCUMENTS							
Examiner Initial		Document Number	Date	Name	Class	Sub-class	Filing Date
	BA	2003/0183940	10/02/03	Noguchi et al.	257	767	
	BB	6,514,852	02/04/03	Usami	438	624	
	BC						
	BD						
	BE						
	BF						
	BG						
	BH						
FOREIGN PATENT DOCUMENTS							
Examiner Initial		Document Number	Date	Country	Class	Sub-class	Translation
	BI	2003-297918	10/17/03	Japan			Abstract
	BJ	2002-43419	02/08/02	Japan			Abstract
	BK	2002-270691	09/20/02	Japan			Abstract
	BL						
	BM						
	BN						
	BO						
	BP						
OTHER (including author, title, date, pertinent pages, etc.)							
	BQ						
Examiner				Date Considered			
EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.							